



20V P-Channel Enhancement Mode MOSFET

Voltage

-20 V

Current

-7.2A

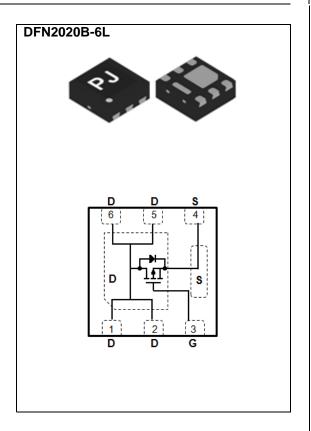
Features

- RDS(ON) , VGS@-4.5V, ID@-7.2A<32mΩ
- RDS(ON) , VGS@-2.5V, ID@-5.0A<39mΩ
- RDS(ON) , VGS@-1.8V, ID@-2.5A<48mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

• Case: DFN2020B-6L Package

• Terminals: Solderable per MIL-STD-750, Method 2026



$\textbf{Maximum Ratings and Thermal Characteristics} \; (T_A = 25 ^{\circ} \text{C unless otherwise noted})$

PARAMETER			UNITS
Drain-Source Voltage		-20	V
Gate-Source Voltage		<u>+</u> 8	V
Continuous Drain Current		-7.2	Α
Pulsed Drain Current		-28.8	Α
T _a =25°C	P _D	2.8	W
Derate above 25°C		22	mW/°C
Operating Junction and Storage Temperature Range		-55~150	°C
Typical Thermal Resistance - Junction to Ambient, t<10s (Note 3)		44.6	°C/W
	Derate above 25°C perature Range	Derate above 25°C PD PD TJ,TSTG	V _{DS} -20 V _{GS} ±8 I _D -7.2 I _{DM} -28.8 T _a =25°C 2.8 Derate above 25°C 22 perature Range T _J ,T _{STG} -55~150





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-20	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-0.35	-0.6	-0.9	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V,I _D =-7.2A	-	25	32	mΩ		
		V _{GS} =-2.5V,I _D =-5.0A	-	30	39			
		V _{GS} =-1.8V,I _D =-2.5A	-	35	48			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V,V _{GS} =0V	-	-0.01	-1.0	uA		
Gate-Source Leakage Current	I _{GSS}	$V_{GS}=\underline{+}8V, V_{DS}=0V$	-	<u>+</u> 10	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	Q_g	V _{DS} =-10V, I _D =-7.2A, V _{GS} =-4.5V ^(Note 1,2)	-	18.9	-	nC		
Gate-Source Charge	Q_gs		-	2.8	-			
Gate-Drain Charge	Q_{gd}		-	4.2	-			
Input Capacitance	Ciss	V _{DS} =-10V, V _{GS} =0V, f=1.0MHZ	-	1785	-	pF		
Output Capacitance	Coss		-	152	-			
Reverse Transfer Capacitance	Crss		-	125	-			
Turn-On Delay Time	td _(on)	V_{DS} =-10V, I_{D} =-7.2A, V_{GEN} =-4.5V, R_{L} =10 Ω	-	12	-			
Turn-On Rise Time	tr		-	68	-	ns		
Turn-Off Delay Time	td _(off)		-	82	-			
Turn-Off Fall Time	tf		-	35	-			
Drain-Source Diode								
Maximum Continuous Drain-Source					1.5	А		
Diode Forward Current	I _S		-	-	-1.5			
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.64	-1.2	V		

NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

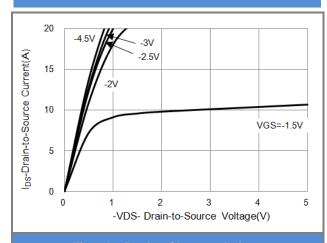


Fig.1 On-Region Characteristics

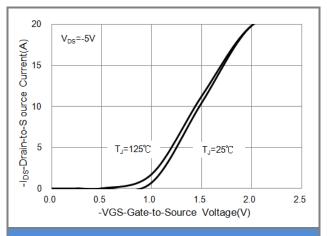


Fig.2 Transfer Characteristics

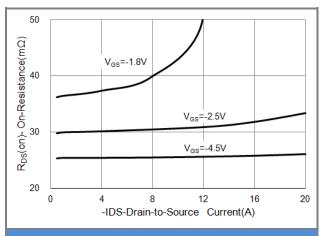


Fig.3 On-Resistance vs. Drain Current

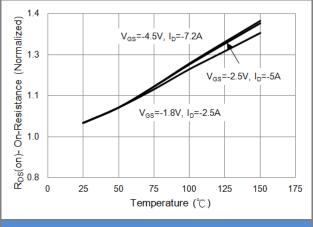


Fig.4 On-Resistance vs. Junction temperature

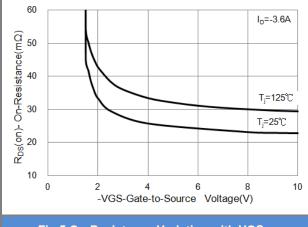


Fig.5 On-Resistance Variation with VGS.

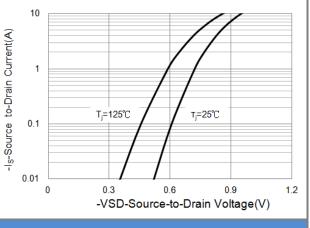


Fig.6 Body Dlode CharacterIslcs





TYPICAL CHARACTERISTIC CURVES

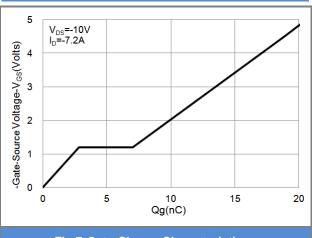


Fig.7 Gate-Charge Characteristics

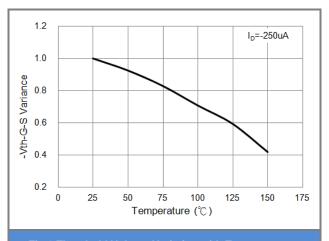


Fig.8 Threshold Voltage Variation with Temperature.

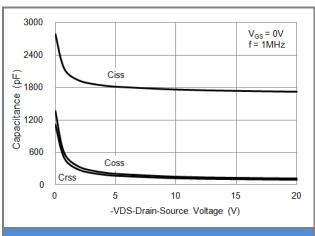


Fig.9 Capacitance vs. Drain-Source Voltage.

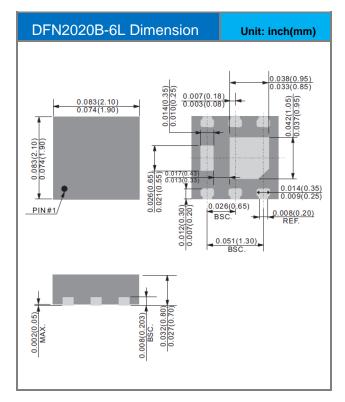


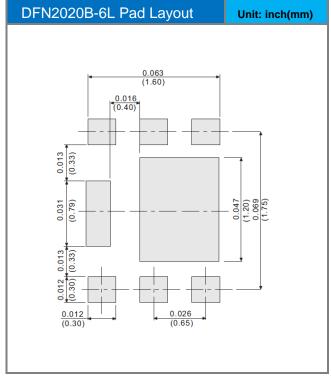


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ2405_R1_00001	DFN2020B-6L	3K pcs / 7" reel	405	Halogen free

MOUNTING PAD LAYOUT









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